

Supporting information

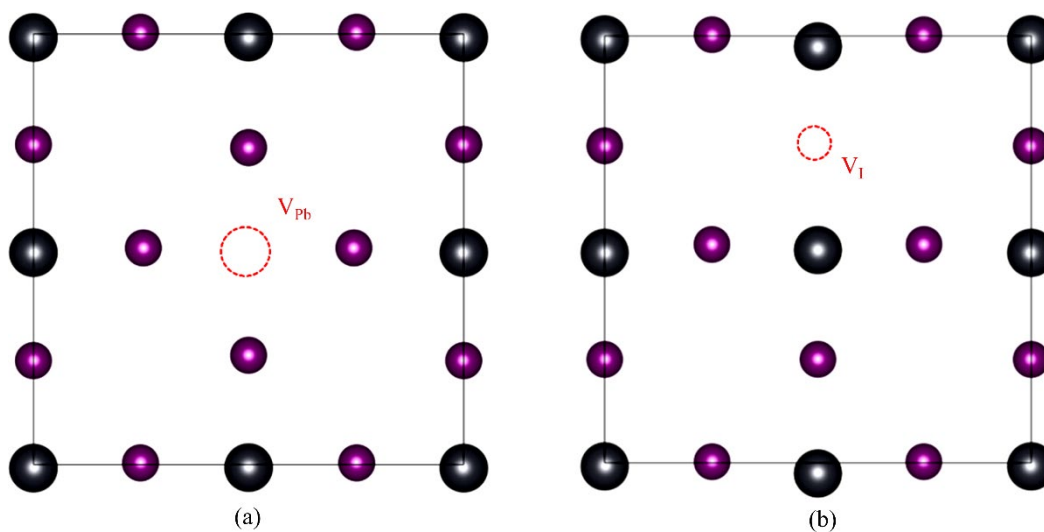


Figure S1 Top view of the defect model: (a) Location map of lead vacancy defects; (b) Location map of iodine vacancy defects

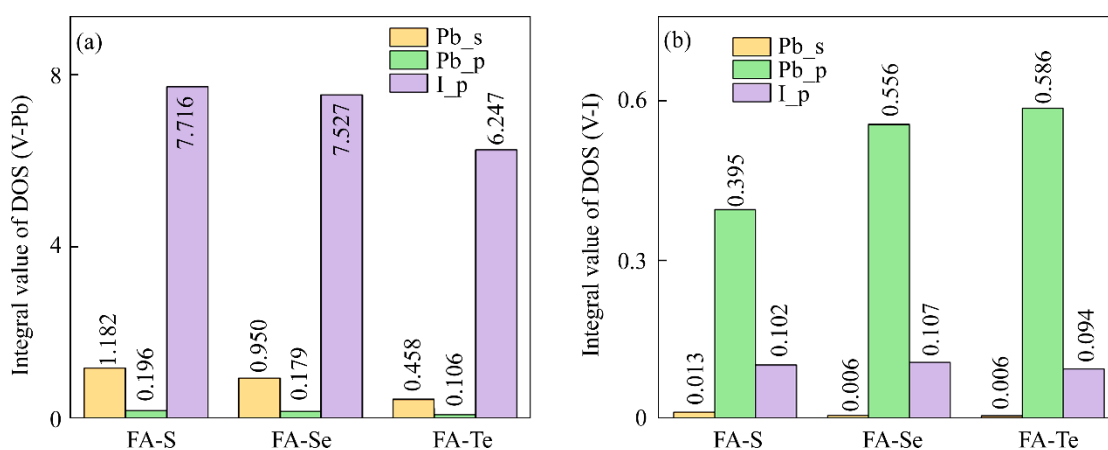


Figure S2 Histogram of the integral PDOS of the FAPbI₃ with PbX covering layer with the integration interval ranges from -0.4 eV to 0.4 eV: (a) Integral value of DOS (V-Pb); (b) Integral value of DOS (V-I)

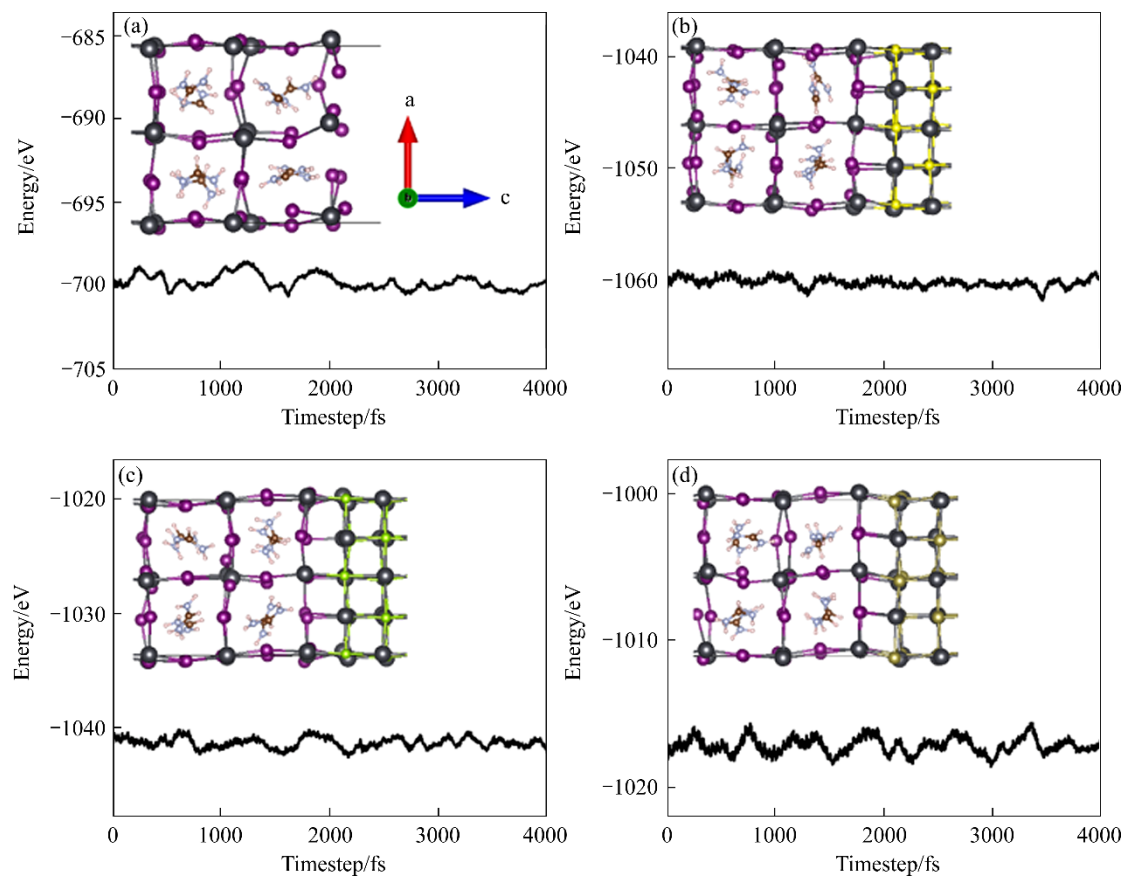


Figure S3 Energy versus time step curve during AIMD simulation of lead vacancy defect perovskite heterojunction: (a) FAPbI₃ (V-Pb); (b) FAPbI₃/PbS (V-Pb); (c) FAPbI₃/PbSe (V-Pb); (d) FAPbI₃/PbS (V-Pb)

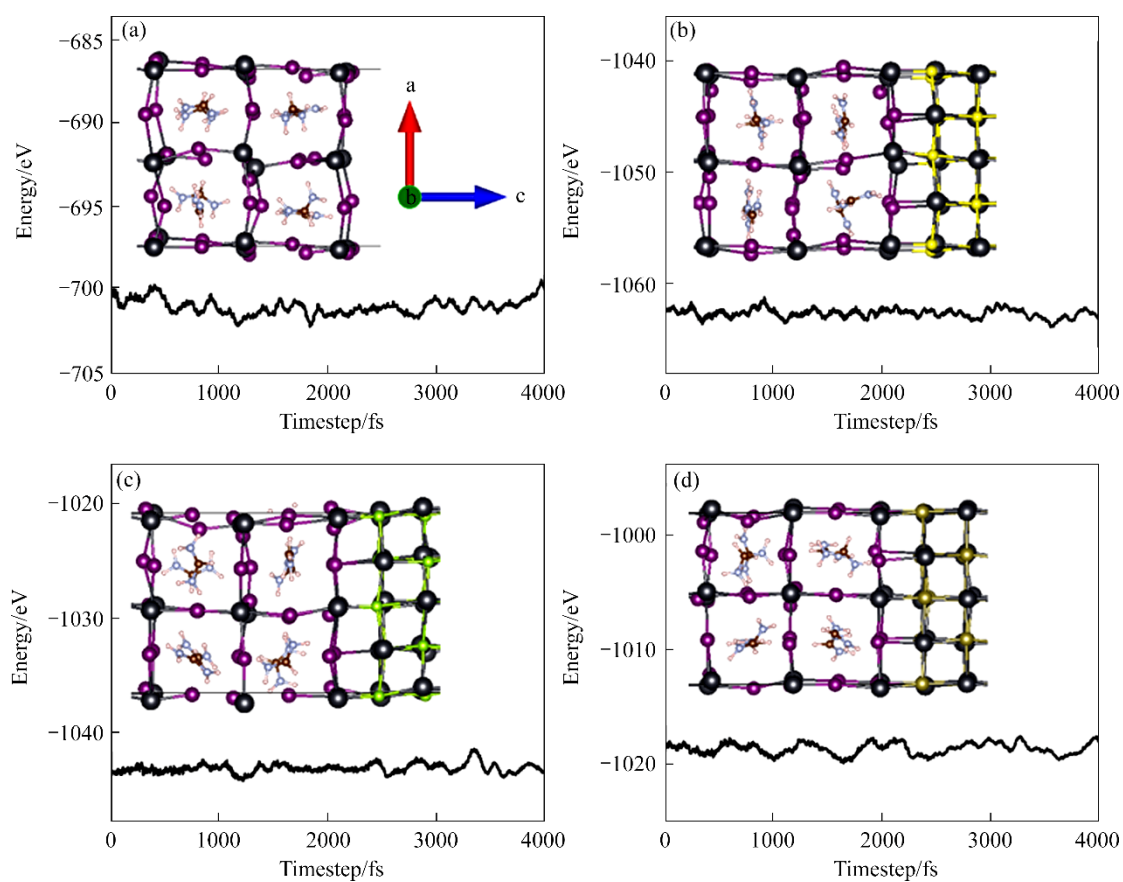


Figure S4 Energy versus time step curve during AIMD simulation of iodine vacancy defect perovskite heterojunction: (a) FAPbI₃ (V-I); (b) FAPbI₃/PbS (V-I); (c) FAPbI₃/PbSe (V-I); (d) FAPbI₃/PbTe (V-I)

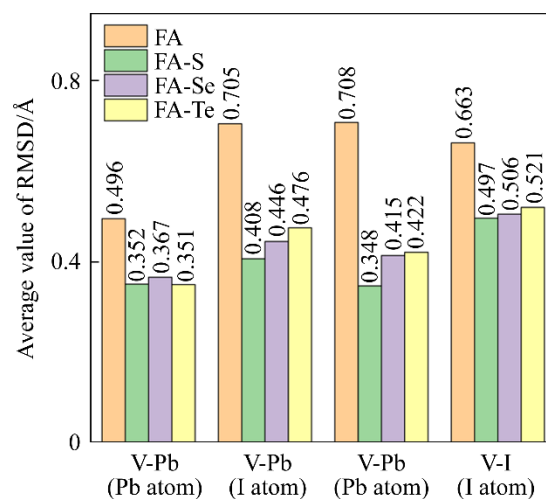


Figure S5 Histogram of the calculated average values of RMSD for Pb and I atoms of FAPbI₃ in FAPbI₃/PbX heterostructure

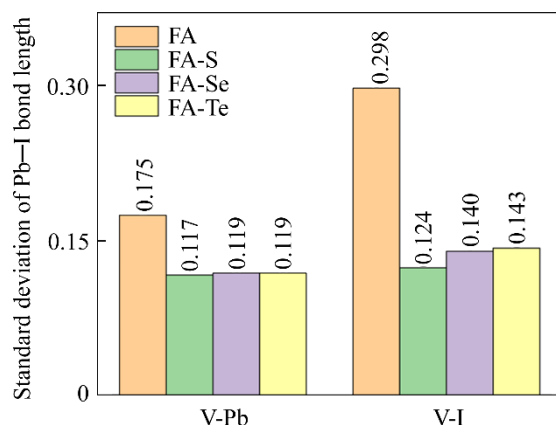


Figure S6 Histogram of the calculated standard deviation of Pb—I bond length fluctuations of FAPbI₃ in FAPbI₃/PbX heterostructure

Table S1 Calculated lattice parameters of FAPbI₃ slabs, PbX slabs and lattice parameters and lattice mismatch ratio of FAPbI₃/PbX heterostructures

Lattice parameter	Before		After	Lattice mismatch ratio/%
	FAPbI ₃	PbX	FAPbI ₃ -PbX	
FAPbI ₃ -PbS	12.83	11.95	12.38	2.36
FAPbI ₃ -PbSe	12.83	12.36	12.59	1.24
FAPbI ₃ -PbTe	12.83	13.08	12.96	0.65

Table S2 Calculated vertical interlayer distances values for the relaxed FAPbI₃-PbX at different interface Å

Interface	FAPbI ₃ /PbS	FAPbI ₃ /PbSe	FAPbI ₃ /PbTe
PbI interface	2.82	2.95	3.13
I interface	3.32	3.20	3.33

Table S3 Calculated average values of RMSD for Pb and I atoms of FAPbI₃ in FAPbI₃/PbX heterostructure with different PbX covering layer Å

Vacancy defect	Atom	FA	FA-S	FA-Se	FA-Te
V-Pb	Pb	0.496	0.352	0.367	0.351
	I	0.705	0.408	0.446	0.476
V-I	Pb	0.708	0.348	0.415	0.422
	I	0.663	0.497	0.506	0.521